

Transistor

Switching (45V, 7.0A)

RSS070N05

●Features

- 1) Built-in G-S Protection Diode.
- 2) Small and Surface Mount Package (SOP8).

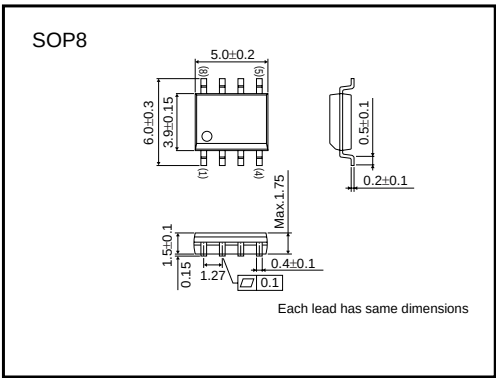
●Applications

Power switching , DC / DC converter , Inverter

●Structure

Silicon N-channel
MOS FET

●External dimensions (Unit : mm)



●Packaging dimensions

Package	Taping
Code	TB
Basic ordering unit(pieces)	2500

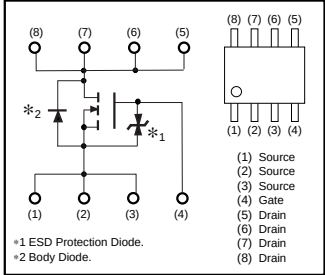
●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DS}	45	V
Gate-source voltage	V_{GS}	20	V
Drain current	Continuous	I_D	±7.0 A
	Pulsed	I_{DP}	±28 A *
Source current (Body diode)	Continuous	I_S	1.6 A
	Pulsed	I_{SP}	28 A *
Total power dissipation	P_D	2	W *
Chanel temperature	T_{ch}	150	°C
Range of Storage temperature	T_{stg}	-55 to +150	°C

*1 $PW \leq 10\mu s$, Duty cycle $\leq 1\%$

*2 Mounted on a ceramic board

●Equivalent circuit



* A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use a protection circuit when the fixed voltage are exceeded.

●Thermal resistance (Ta=25°C)

Parameter	Symbol	Limits	Unit
Chanel to ambient	$R_{th(ch-a)}$	62.5	°C/W *

*2 Mounted on a ceramic board

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Gate-source leakage	I_{GSS}	—	—	10	μA	$V_{GS}=20V/V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	45	—	—	V	$I_D=1mA/V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS}=45V/V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	—	2.5	V	$V_{DS}=10V/I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	—	18	25	m Ω	$I_D=7A/V_{GS}=10V$
		—	23	32		$I_D=7A/V_{GS}=4.5V$
		—	25	35		$I_D=7A/V_{GS}=4.0V$
Forward transfer admittance	$ Y_{fs} $ *	6.0	—	—	S	$V_{DS}=10V/I_D=7A$
Input capacitance	C_{iss}	—	1000	—	pF	$V_{DS}=10V$
Output capacitance	C_{oss}	—	230	—		$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	—	125	—		$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	—	16	—	ns	$V_{DD}=25V$
Rise time	t_r *	—	27	—		$I_D=3.5A$
Turn-off delay time	$t_{d(off)}$ *	—	57	—		$V_{GS}=10V$
Fall time	t_f *	—	21	—		$R_L=7.1\Omega/R_G=10\Omega$
Total gate charge	Q_g *	—	12.0	16.8	nC	$V_{DD}=25V/I_D=7A$
Gate-source charge	Q_{gs} *	—	3.0	—		$V_{GS}=5V$
Gate-drain charge	Q_{gd} *	—	4.6	—		$R_L=3.6\Omega/R_G=10\Omega$

* pulsed

●Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward voltage	V_{SD} *	—	—	1.2	V	$I_S=1.6A/V_{GS}=0V$

* pulsed

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●Electrical characteristic curves

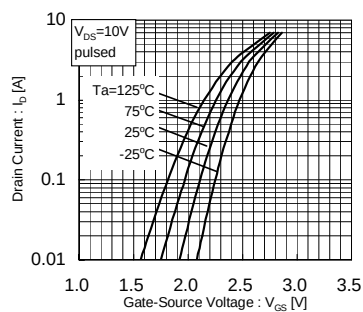


Fig.1 Typical Transfer Characteristics

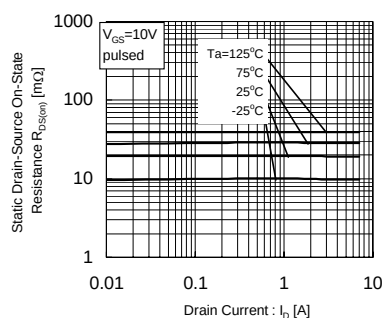


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (1)

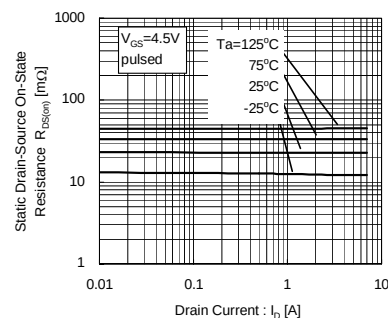


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (2)

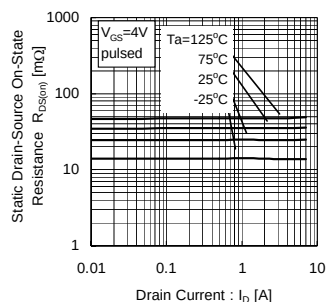


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (3)

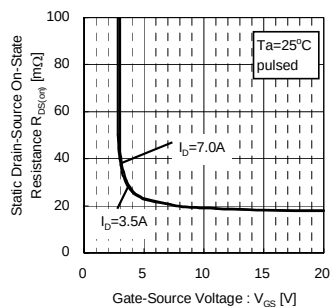


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

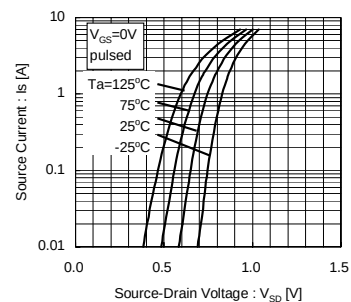


Fig.6 Source-Current vs. Source-Drain Voltage

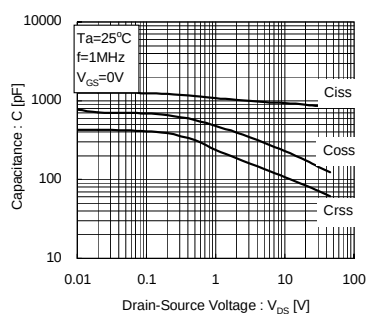


Fig.7 Typical capacitance vs. Source-Drain Voltage

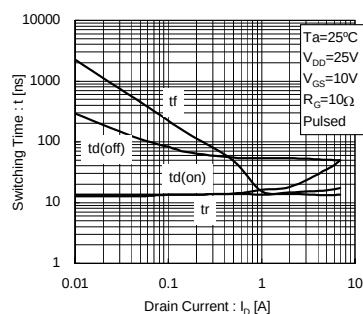


Fig.8 Switching Characteristics

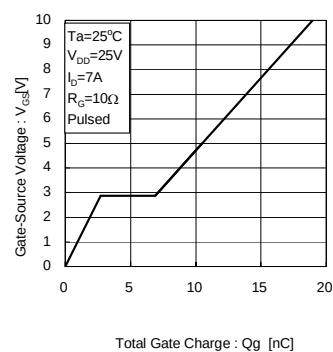


Fig.9 Dynamic Input Characteristics

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●Measurement circuits

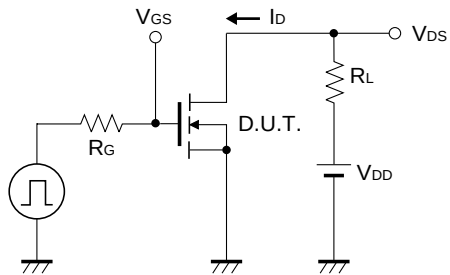


Fig.10 Switching Time Test Circuit

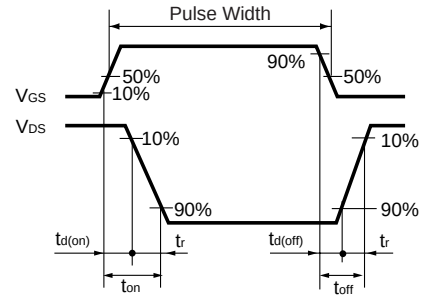


Fig.11 Switching Time Waveforms

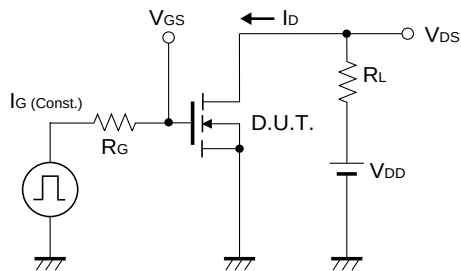


Fig.12 Gate Charge Test Circuit

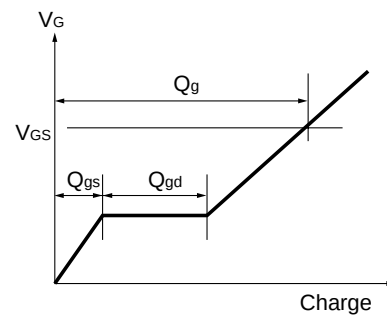


Fig.13 Gate Charge Waveform

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